

STD17NF03L STD17NF03L-1

N-channel 30V - 0.038Ω - 17A - DPAK/IPAK STripFET™ II Power MOSFET

General features

Туре	V _{DSS}	V _{DSS} R _{DS(on)}	
STD17NF03L-1	30V	<0.05Ω	17A
STD17NF03L	30V	<0.05Ω	17A

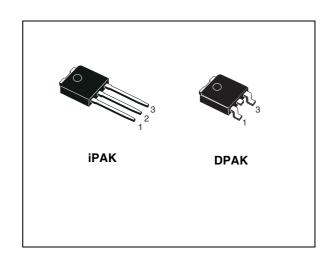
- Exceptional dv/dt capability
- Low gate charge at 100°C
- Application oriented characterization
- 100% avalanche tested



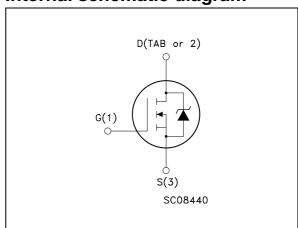
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature SizeTM" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

■ Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STD17NF03L-1	D17NF03L@	IPAK	Tube
STD17NF03LT4	D17NF03L@	DPAK	Tape & reel

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit	
V _{DS}	Drain-source voltage (V _{GS} = 0)	30	V	
V _{DGR}	Drain-gate voltage (R_{GS} = 20 kΩ)	30	V	
V _{GS}	Gate- source voltage	± 16	V	
I _D	Drain current (continuous) at T _C = 25°C	17	Α	
I _D	Drain current (continuous) at T _C = 100°C	12	Α	
I _{DM} ⁽¹⁾	Drain current (pulsed)	68	Α	
P _{tot}	Total dissipation at T _C = 25°C	30	W	
	Derating Factor	0.2	W/°C	
dv/dt ⁽²⁾	Peak diode recovery avalanche energy	7	V/ns	
E _{AS} (3)	Single pulse avalanche energy	200	mJ	
T _{stg}	Storage temperature	55 to 175	°C	
Tj	Max. operating junction temperature	55 to 175 °C		

^{1.} Pulse width limited by safe operating area.

Table 2. Thermal data

Rthj-case	Thermal resistance junction-case max	5.0	°C/W
Rthj-amb	Thermal resistance junction-to ambient max	100	°C/W
T _J	T _J Maximum lead temperature for soldering purpose		

^{2.} $I_{SD} \le 7A$, $di/dt \le 300A/\mu s$, $V_{DD} = V_{(BR)DSS}$, $T_j \le T_{JMAX}$

^{3.} Starting $T_j = 25$ °C, $I_D = 8.5$ A, $V_{DD} = 15$ V

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	30			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = Max rating V_{DS} = Max rating, T_{C} = 125°C			1 10	μ Α μ Α
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 16V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1	1.5	2.2	V
R _{DS(on)}	Static drain-source on resistance	$V_{GS} = 10V, I_D = 8.5A$ $V_{GS} = 5V, I_D = 8.5A$		0.038 0.045	0.05 0.06	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
9 _{fs} (1)	Forward transconductance	$V_{DS} > I_{D(on)} x$ $R_{DS(on)max}$, $I_{D} = 8.5A$		12		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		320 155 28		pF pF pF
$\begin{array}{c} t_{\text{d(on)}} \\ t_{\text{r}} \\ t_{\text{d(off)}} \\ t_{\text{f}} \end{array}$	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 15V, I_D = 8.5A R_G = 4.7 Ω V_{GS} = 5V (see <i>Figure 13</i>)		11 100 25 22		ns ns ns
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 3024V, I_{D} = 17A,$ $V_{GS} = 5V, R_{G} = 4.7\Omega$ (see <i>Figure 14</i>)		4.8 2.25 1.7	6.5	nC nC nC

^{1.} Pulsed: Pulse duration = 300 μs, duty cycle 1.5%.

Table 5. Source drain diode

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current Source-drain current (pulsed)				22 88	A A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 17A, V _{GS} = 0			1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 17A$, di/dt = 100A/ μ s, $V_{DD} = 15V$, $T_{j} = 150$ °C (see <i>Figure 15</i>)		28 18 1.3		ns nC A

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: Pulse duration = 300 μ s, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Thermal impedance

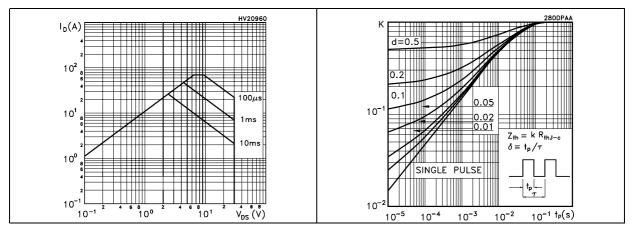


Figure 3. Output characteristics

Figure 4. Transfer characteristics

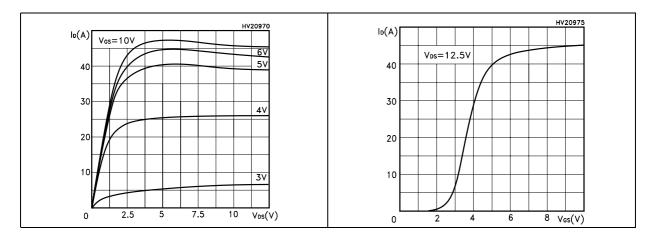
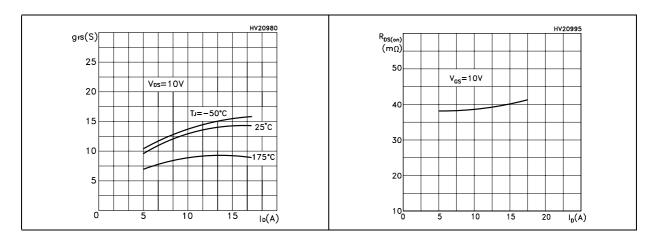


Figure 5. Transconductance

Figure 6. Static drain-source on resistance



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Figure 7. Gate charge vs. gate-source voltage Figure 8. Capacitance variations

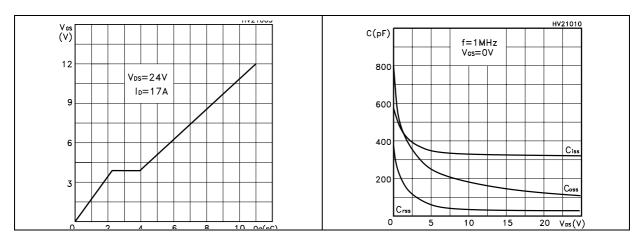


Figure 9. Normalized gate threshold voltage Figure 10 vs. temperature

Figure 10. Normalized on resistance vs. temperature

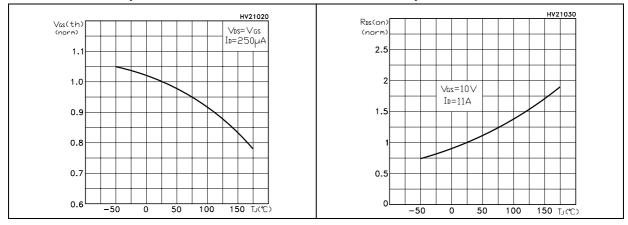
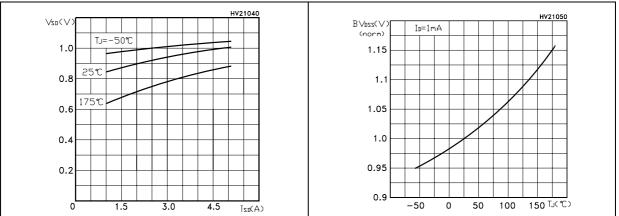


Figure 11. Source-drain diode forward characteristics

Figure 12. Normalized breakdown voltage vs. temperature



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3 Test circuit

Figure 13. Switching times test circuit for resistive load

Figure 14. Gate charge test circuit

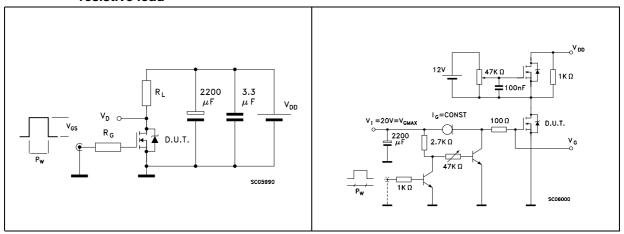


Figure 15. Test circuit for inductive load switching and diode recovery times

Figure 16. Unclamped Inductive load test circuit

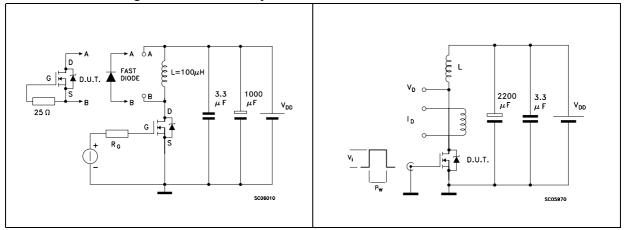
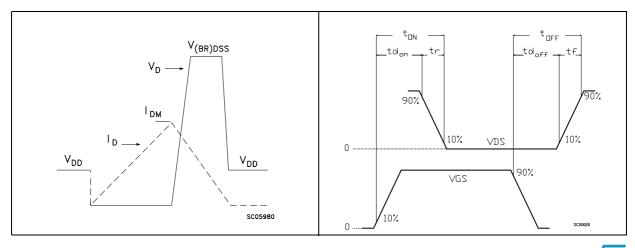


Figure 17. Unclamped inductive waveform

Figure 18. Switching time waveform



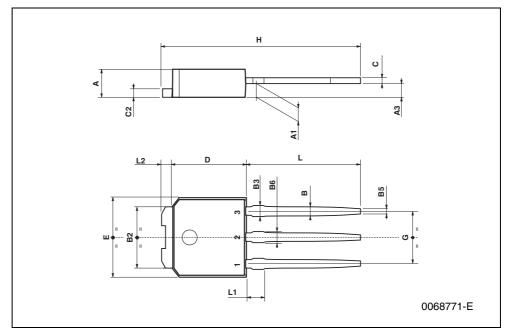
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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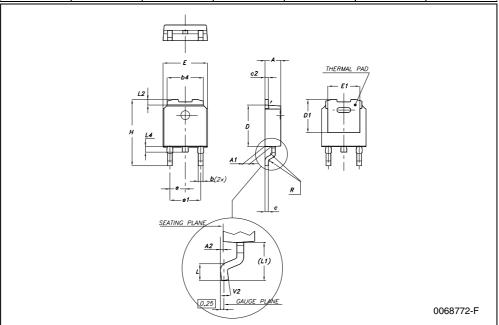
TO-251 (IPAK) MECHANICAL DATA

DIM.		mm			inch	
Dilvi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
В	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
С	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
Н	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



DPAK MECHANICAL DATA

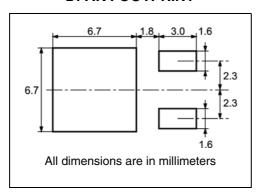
DIM		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
С	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
Е	6.4		6.6	0.252		0.260
E1		4.7			0.185	
е		2.28			0.090	
e1	4.4		4.6	0.173		0.181
Н	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°



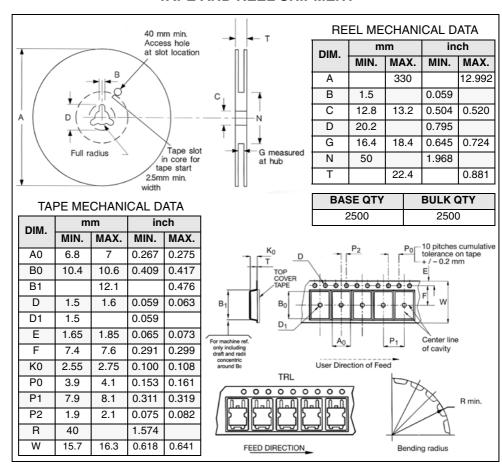
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5 Packing mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT



6 Revision history

Table 6. Revision history

Date	Revision	Changes
19-Oct-2004	1	First release
20-Nov-2004	2	Modified value in title
03-Jul-2006	3	New template, no content change
19-Feb-2007	4	Typo mistake on page 1

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